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Kind regards,

Team Nexperia

Product data sheet

1. General description

High power density, hyperfast PN-rectifier with high-efficiency planar technology, encapsulated in a small and flat lead SOD123W Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Reverse voltage V_R ≤ 200 V
- Forward current I_F ≤ 2 A
- Hyperfast recovery time t_{rr} ≤ 25 ns
- Pt doped life time control
- Low inductance
- Small and flat lead SMD plastic package
- Package height typ. 1 mm
- High power capability due to clip-bond technology
- · Planar die design

3. Applications

- · General-purpose rectification
- Reverse polarity protection
- Hyperfast switching
- Freewheeling applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$I_{F(AV)}$	average forward current	δ = 0.5 ; f = 20 kHz; square wave; $T_{sp} \le 139 ^{\circ}\text{C}$		-	-	2	Α
V_{RRM}	repetitive peak reverse voltage	T _j = 25 °C		-	-	200	V
V_R	reverse voltage			-	-	200	V
V _F	forward voltage	I _F = 2 A; pulsed; T _j = 25 °C	[1]	-	890	950	mV
		I _F = 2 A; pulsed; T _j = 125 °C	[1]	-	750	825	mV
I _R	reverse current	V _R = 200 V; pulsed; T _j = 25 °C	[1]	-	5	200	nA
		V _R = 200 V; pulsed; T _j = 125 °C	[1]	-	1.5	20	μΑ

^[1] Very short test pulse to keep the junction termperature unchanged.



200 V, 2 A hyperfast PN-rectifier

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	1 2	1 2
2	Α	anode	SOD123W	006aab040

6. Ordering information

Table 3. Ordering information

Type number		Package					
		Name	Description	Version			
	ES2DVR	SOD123W	plastic surface mounted package; 2 leads	SOD123W			

7. Marking

Table 4. Marking codes

Type number	Marking code
ES2DVR	KL

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage	T _j = 25 °C		-	200	V
V_R	reverse voltage			-	200	V
V _{RMS}	RMS voltage			-	140	V
I _F	forward current	δ = 1 ; T _{sp} ≤ 135 °C		-	2.83	Α
$I_{F(AV)}$	average forward current	δ = 0.5 ; f = 20 kHz; square wave; T _{sp} ≤ 139 °C		-	2	А
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; single half sine wave (applied at rated load condition)		-	40	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	735	mW
			[2]	-	1.19	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	170	K/W
			[2]	-	-	105	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[3]	-	-	15	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[3] Soldering point of cathode tab.

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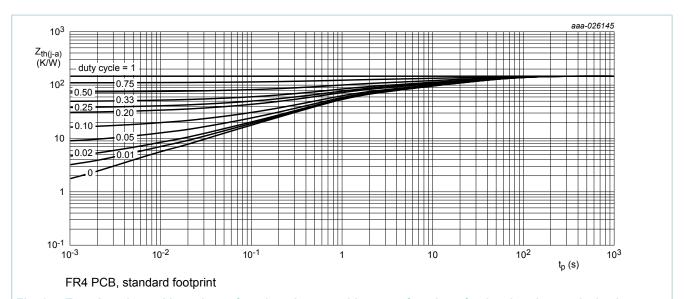


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

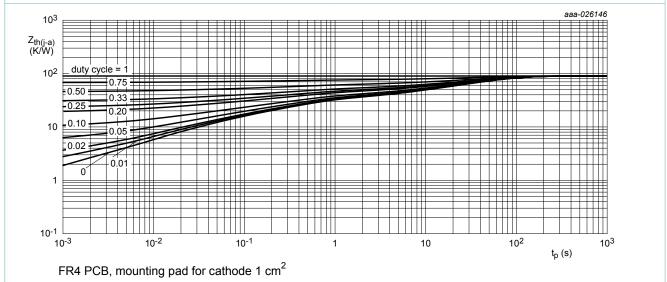


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)R}	reverse breakdown voltage	I_R = 100 μ A; T_j = 25 °C; pulsed	[1]	200	-	-	V
V _F	forward voltage	I _F = 2 A; pulsed; T _j = 25 °C	[1]	-	890	950	mV
		I _F = 2 A; pulsed; T _j = 125 °C	[1]	-	750	825	mV
I _R	reverse current	V _R = 200 V; pulsed; T _j = 25 °C	[1]	-	5	200	nA
		V _R = 200 V; pulsed; T _j = 125 °C	[1]	-	1.5	20	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 4 V; T _j = 25 °C		-	20	-	pF
t _{rr}	reverse recovery time; step recovery	$I_F = 0.5 \text{ A}$; $I_R = 1 \text{ A}$; $I_{R(meas)} = 0.25 \text{ A}$; $T_j = 25 \text{ °C}$		-	10	25	ns
	reverse recovery time; ramp recovery	$I_F = 1 \text{ A}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_j = 25 \text{ °C}$		-	20	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$		-	930	-	mV

[1] Very short test pulse to keep the junction termperature unchanged.

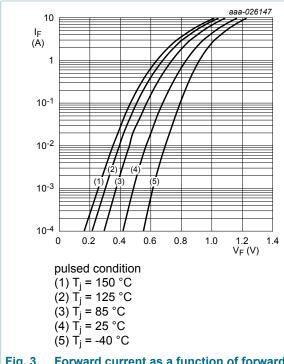


Fig. 3. Forward current as a function of forward voltage; typical values

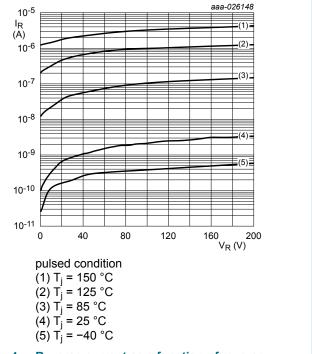


Fig. 4. Reverse current as a function of reverse voltage; typical values

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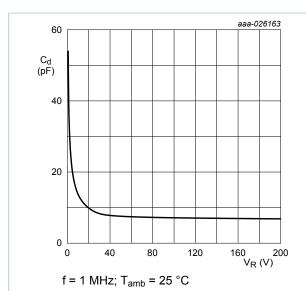
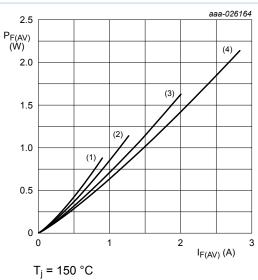
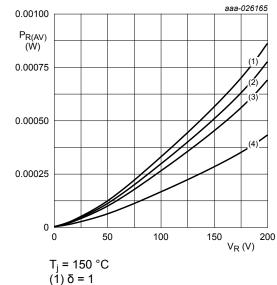


Fig. 5. Diode capacitance as a function of reverse voltage; typical values



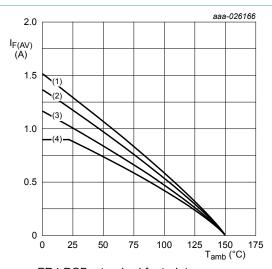
 $T_j = 150 \,^{\circ}\text{C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$ (3) $\delta = 0.5$ (4) $\delta = 0.8$ (5) $\delta = 1$

Fig. 6. Average forward power dissipation as a function of average forward current; typical values



 $(1) \delta = 1$ $(2) \delta = 0.9$ $(3) \delta = 0.8$ $(4) \delta = 0.5$

Fig. 7. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_j = 150 \,^{\circ}\text{C}$ (1) $\delta = 1$; DC

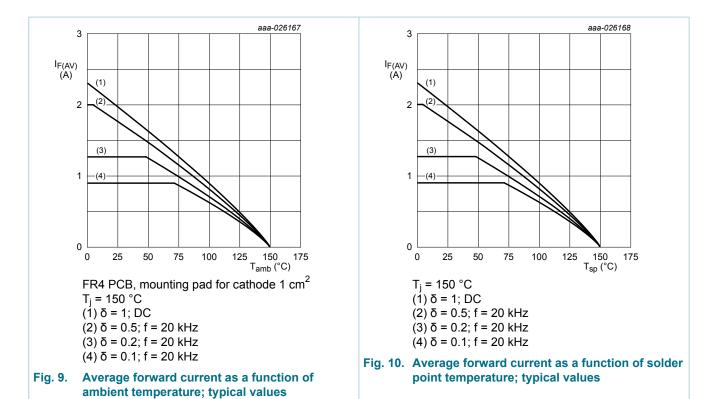
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

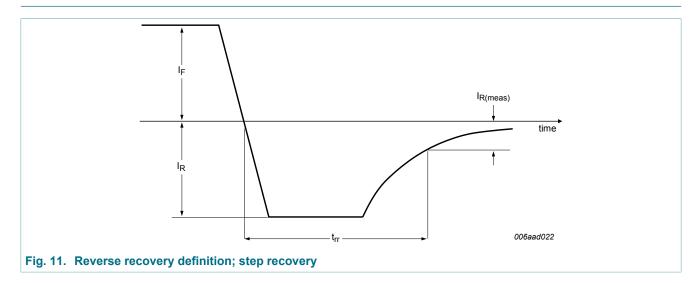
(4) δ = 0.1; f = 20 kHz

Fig. 8. Average forward current as a function of ambient temperature; typical values

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11. Test information



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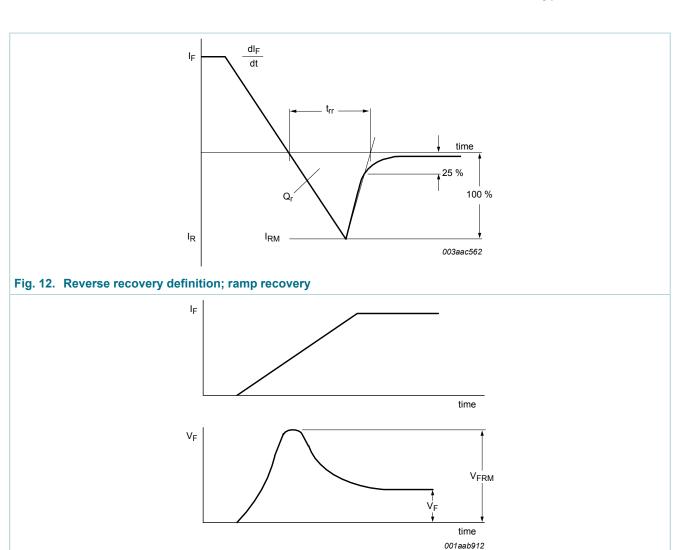


Fig. 13. Forward recovery definition

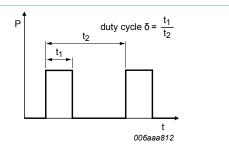
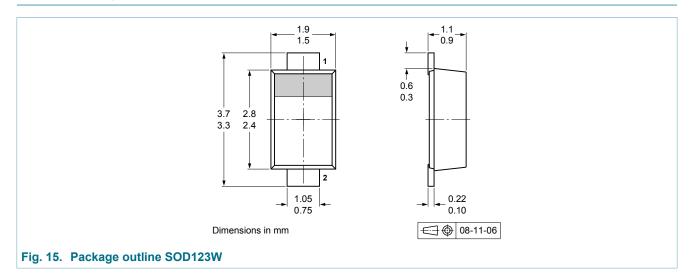


Fig. 14. Duty cycle definition

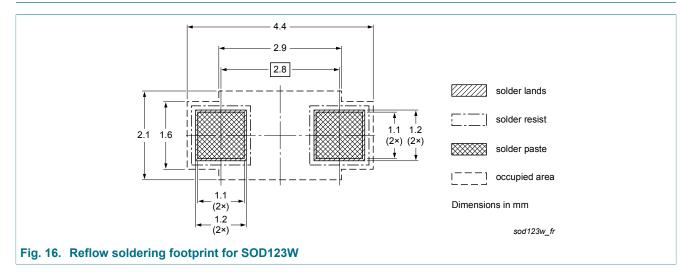
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_{M} \times \delta$ with I_{M} defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_{M} \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
ES2DVR v.2	20170112	Product data sheet	-	ES2DVR v.1			
Modifications:	Product status changed						
ES2DVR v.1	20160930	Objective data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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